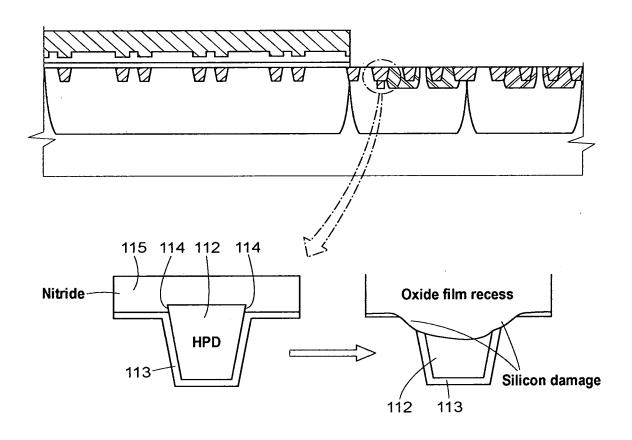
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FIG. 1 PRIOR ART



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FIG. 2A

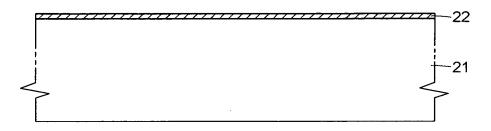
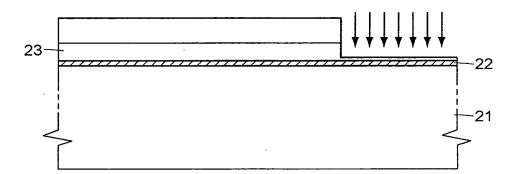


FIG. 2B



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FIG. 2C

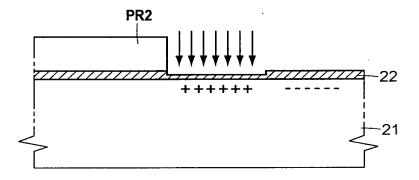


FIG. 2D

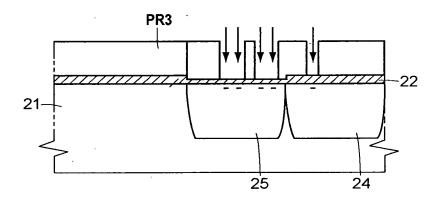
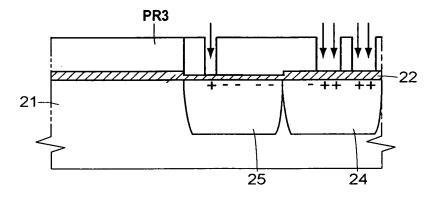


FIG. 2E



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FIG. 2F

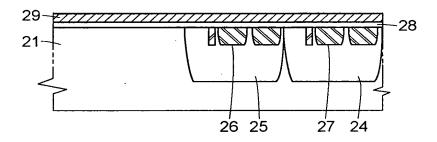
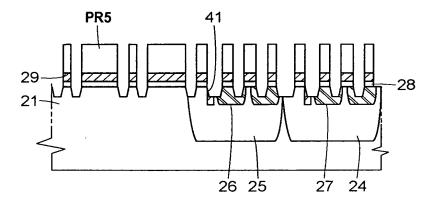


FIG. 2G



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FIG. 2H

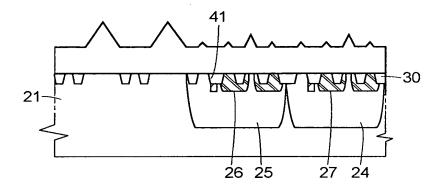


FIG. 21

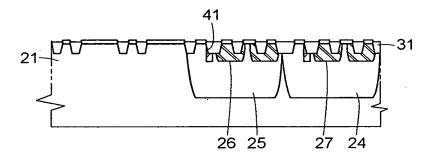
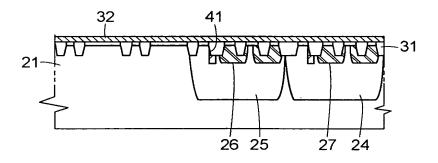


FIG. 2J



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FIG. 2K

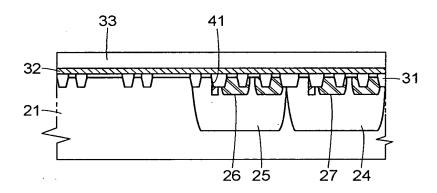
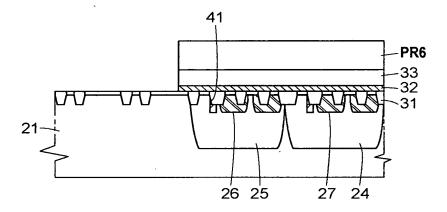


FIG. 2L



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FIG. 2M

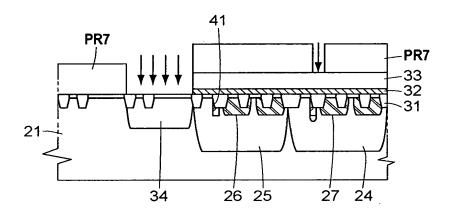


FIG. 2N

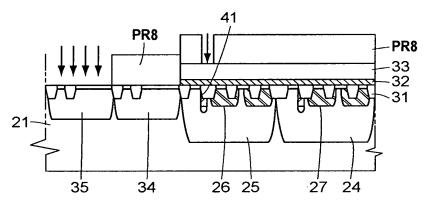
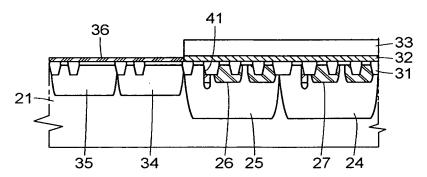


FIG. 20



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FIG. 2P

